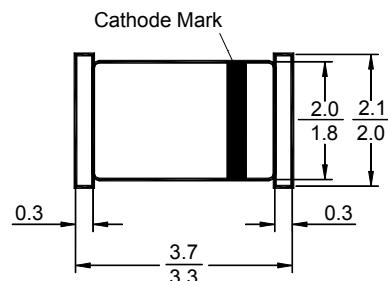


# LM5817 THRU LM5819

## SURFACE MOUNT SCHOTTKY BARRIER DIODES

### Features

- Low switching losses
- Fast recovery time
- Guard ring protected
- Hermetically sealed glass SMD package.



### APPLICATIONS

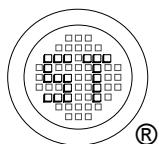
- Low power, switched-mode power supplies
- Rectifying
- Polarity protection

Plastic case MiniMELF  
Dimensions in mm

### Absolute Maximum Ratings and Characteristics (Ratings at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.)

Parameter	Symbols	LM5817	LM5818	LM5819	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	V
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	24	36	48	V
Continuous Reverse Voltage	$V_R$	20	30	40	V
Crest Working Reverse Voltage	$V_{RWM}$	20	30	40	V
Average Forward Current ( $T_{amb} = 60^{\circ}\text{C}$ )	$I_{(AV)}$	1			A
Non-repetitive Peak Forward Current $t = 10\text{ ms half sine wave}; T_j = T_{jmax}$ prior to surge: $V_R = 0$	$I_{FSM}$	25			A
Forward Voltage at $I_F = 0.1\text{ A}$ at $I_F = 1\text{ A}$ at $I_F = 3\text{ A}$	$V_F$	0.32 0.45 0.75	0.33 0.55 0.875	0.34 0.6 0.9	V
Reverse Current at $V_R = V_{RRMmax}^{1)}$ at $V_R = V_{RRMmax} T_j = 100^{\circ}\text{C}$	$I_R$	1 10			mA
Thermal Resistance $R_{\theta JA}$ $R_{\theta JL}$		150 60			K/W
Typical Diode Capacitance at $V_R = 4\text{ V}, f = 1\text{ MHz}$	$C_D$	70	50	50	pF
Junction Temperature	$T_J$	125			°C
Storage Temperature Range	$T_S$	-65 to +175			°C

<sup>1)</sup> Pulse test:  $t_p = 300\text{ }\mu\text{s}; \delta = 0.02$



## LM5817 THRU LM5819

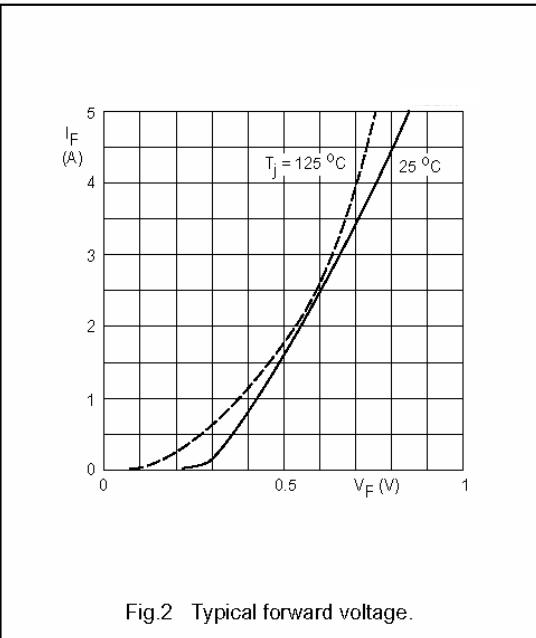


Fig.2 Typical forward voltage.

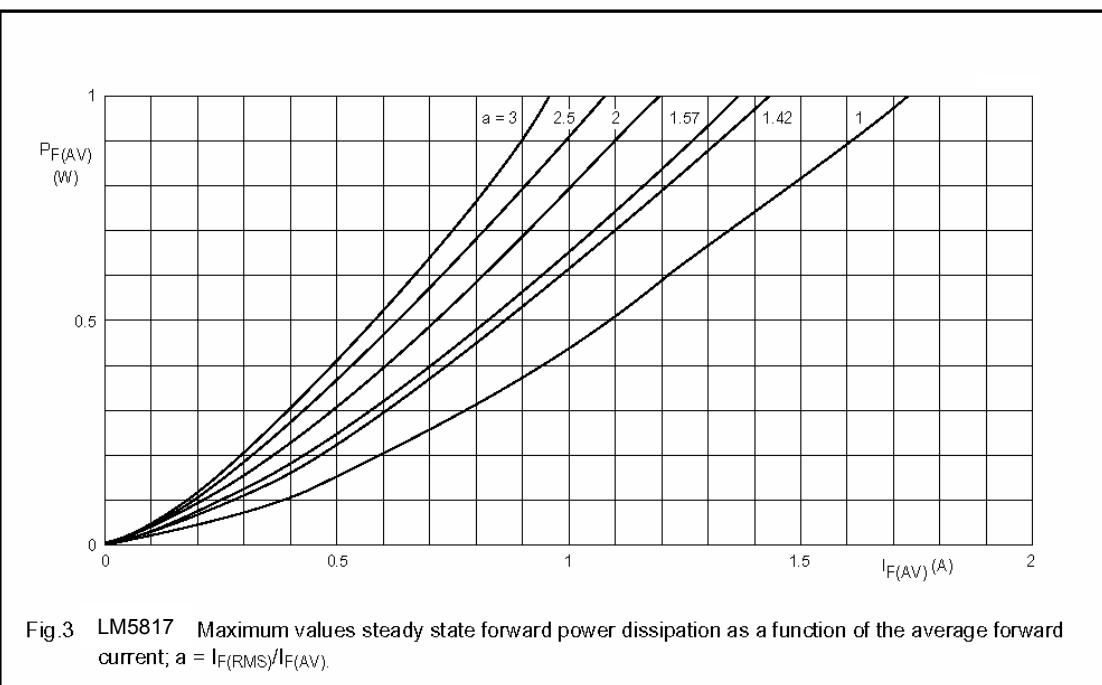
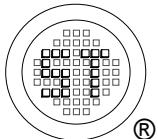


Fig.3 LM5817 Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(\text{RMS})}/I_{F(\text{AV})}$ .



## LM5817 THRU LM5819

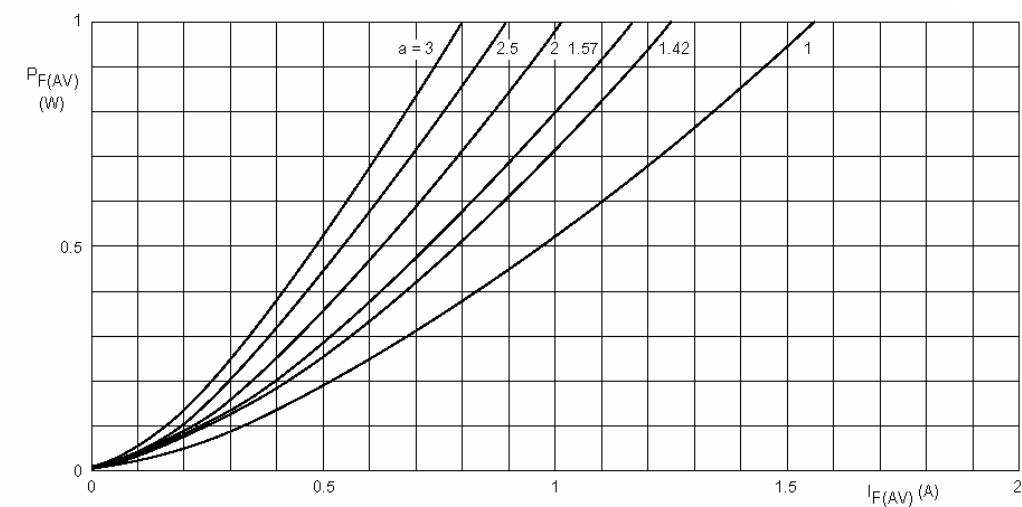


Fig.4 LM5818 Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(\text{RMS})}/I_{F(\text{AV})}$ .

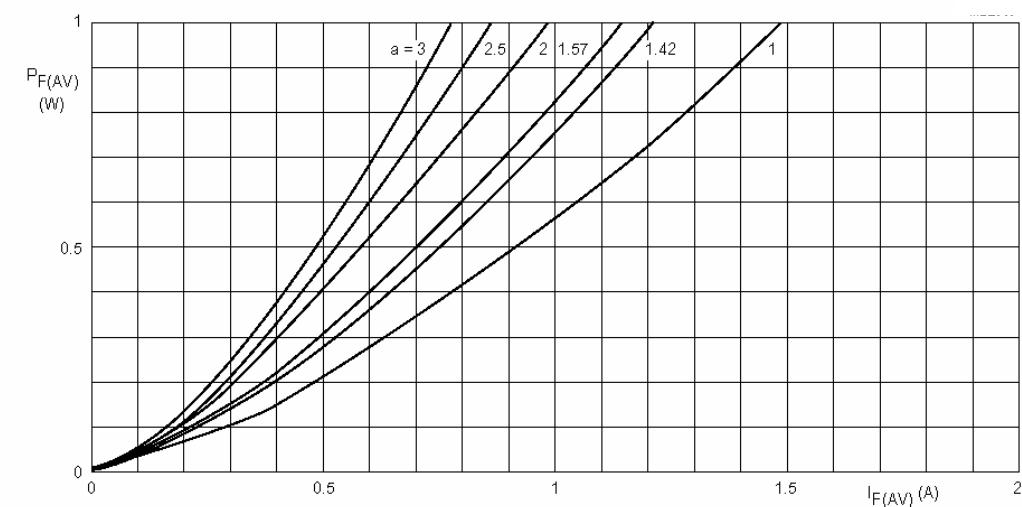
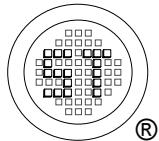


Fig.5 LM5819 Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(\text{RMS})}/I_{F(\text{AV})}$ .



# LM5817 THRU LM5819

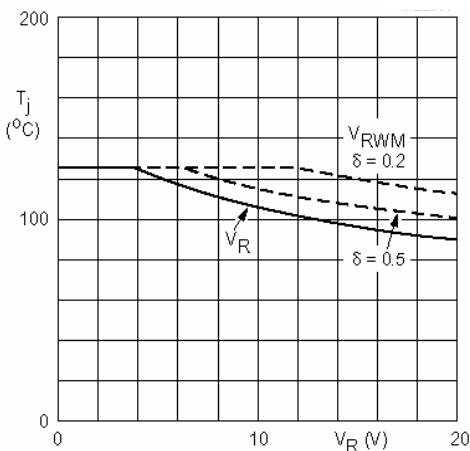


Fig.6 LM5817 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

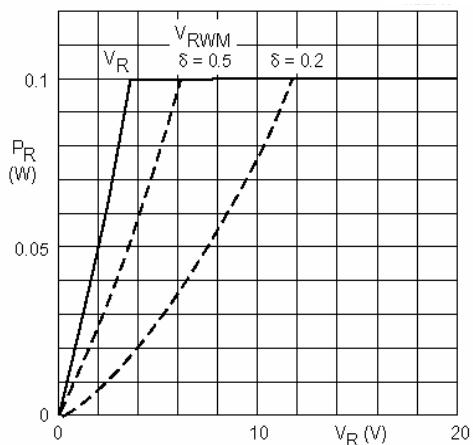


Fig.7 LM5817 Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

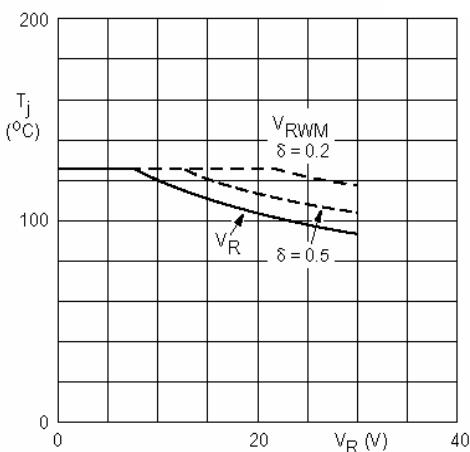


Fig.8 LM5818 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

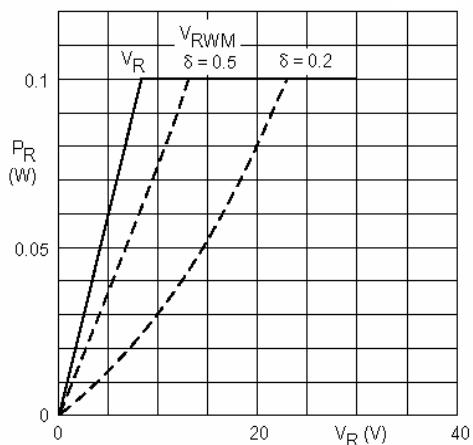
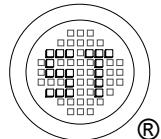


Fig.9 LM5818 i. Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.



## LM5817 THRU LM5819

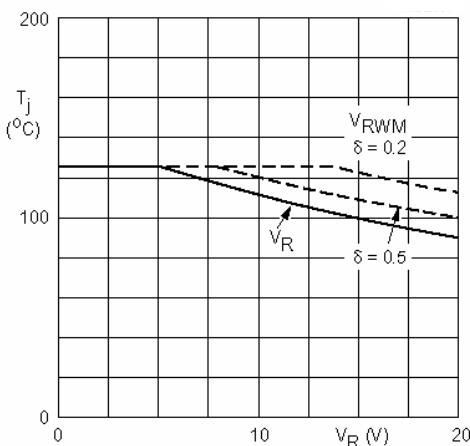


Fig.10 LM5819 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

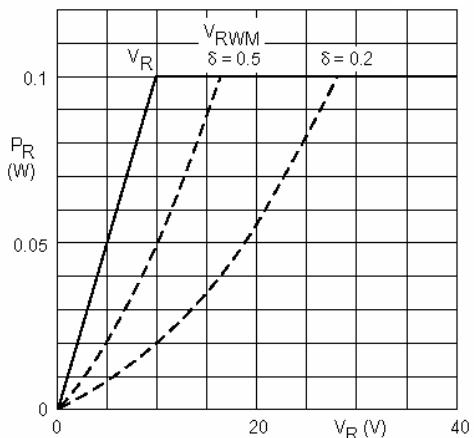


Fig.11 LM5819 Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

